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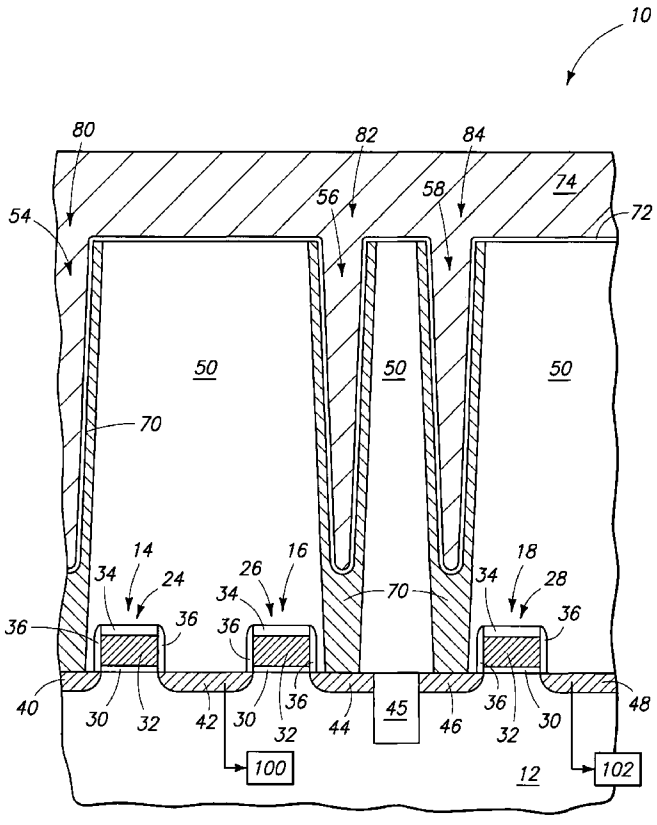
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(54) **Title:** METHODS OF ETCHING INTO SILICON OXIDE-CONTAINING MATERIAL, METHODS OF FORMING CONTAINER CAPACITORS, AND METHODS OF FORMING DRAM ARRAYS



(57) **Abstract:** Methods of etching into silicon oxide-containing material with an etching ambient having at least 75 volume percent helium. The etching ambient may also include carbon monoxide, O_2 and one or more fluorocarbons. The openings formed in the silicon oxide-containing material may be utilized for fabrication of container capacitors, and such capacitors may be incorporated into DRAM.

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